

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

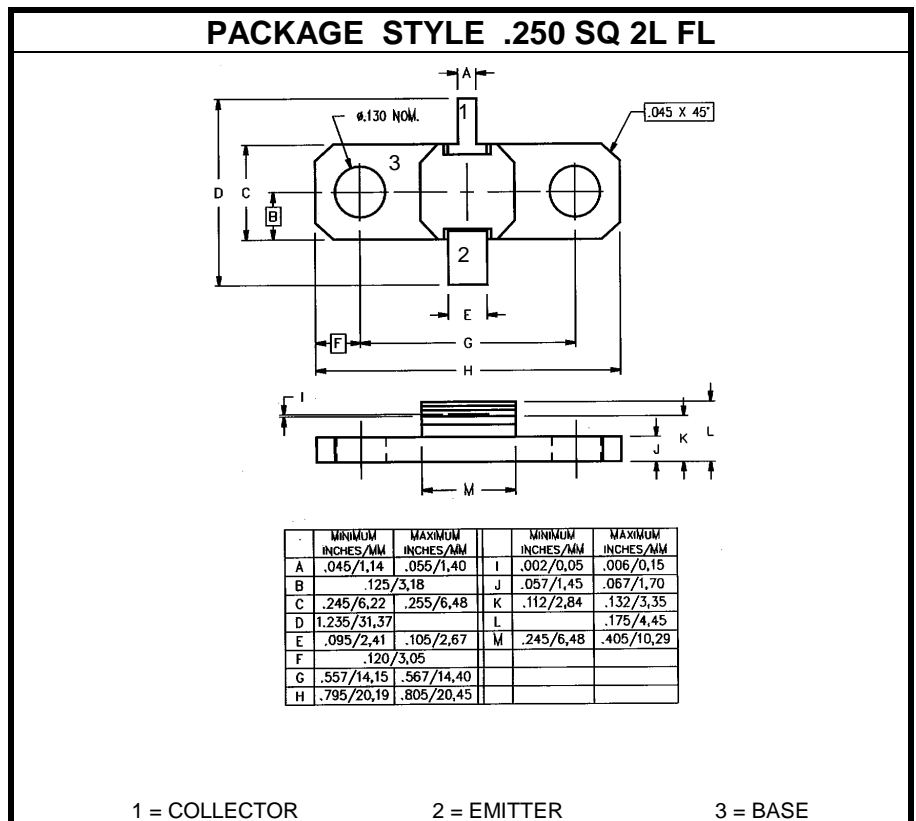
The **ASI SD1534-08** is a Common Base Device Designed for DME IFF, and TACAN Pulse Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Emitter Ballasting

MAXIMUM RATINGS

I_C	5.5 A
V_{CES}	65 V
P_{DISS}	218 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	0.80 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			
BV_{CES}	$I_C = 25$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CES}	$V_{CE} = 50$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	10		200	---
P_G	$V_{CC} = 50$ V $P_{IN} = 13.5$ W $f = 1025$ to 1150 MHz	7.5			dB
P_{OUT}	PULSE WIDTH = 10 μS DUTY CYCLE = 1.0%	75			W